

VERSION SHOWING THE CHANGES TO THE SPECIFICATION

IN THE SPECIFICATION:

Amend the specification as follows:

Page 1:

Description

~~[0001]—Electronic Component Comprising Predominantly Organic Functional Materials and a Process for the Production Thereof~~

Paragraph [00016]

[00016] Figure 3 again shows the same structure in another stage in the process, where two further layers 4 and 5 which can comprise semiconducting or insulating material have already been applied over the through plating 3 of Fig. 2 and form fillets with the through plating comprising the upwardly inclined raised portions of each layer at their junctions with the through plating. See also Fig. 4. The following for example can be used as semiconductor: polyalkthiophene or polyfluorene, while the insulator used can be for example polyhydroxystyrene, polymethrethacrylate or polystyrene. By virtue of its size and/or its nature the through-plating 3 passes through the two central functional layers 4, 5 and thus forms the desired contact.

Paragraph [0022] of the published application:

[0022] The disruption 7, Fig. 8, provides that, around it, the subsequently applied central functional layer 4 or layers 4, 5 tears or tear open (as manifested by the larger region of the layer 6 contiguous with the layer 2 next adjacent to the disruption 7, Fig. 8) and/or is or, in the alternative, the layer 4 as shown in Figs. 5-7 (or layers 4 and 5) are absent, in the region of the through plating 3 being shown mounted directly on the layer 2, due to non-wetting or in

some other fashion, by the presence of the non-wetting element on the layer 2,
so that a region is produced around the disruption 7, Fig. 8, (or as in Figs. 3-7,
a void is created in the layers due to the presence of the non-wetting element,
e.g., the through plating 3, or its equivalent),- in which the lower layer 2 to be
contacted, as per Fig. 8, is exposed, in the operation of forming the upper layer
6 to be contacted.